3.3V CMOS Static RAM 4 Meg (512K x 8-Bit)

IDT71V424S IDT71V424L

Features

- 512K x 8 advanced high-speed CMOS Static RAM
- ◆ JEDEC Center Power / GND pinout for reduced noise
- Equal access and cycle times
 Commercial and Industrial: 10/12/15ns
- Single 3.3V power supply
- One Chip Select plus one Output Enable pin
- Bidirectional data inputs and outputs directly TTL-compatible
- Low power consumption via chip deselect
- Available in 36-pin, 400 mil plastic SOJ package and 44-pin, 400 mil TSOP.

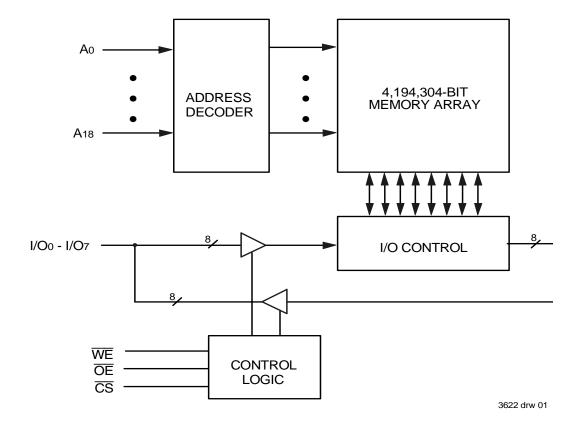
Description

The IDT71V424 is a 4,194,304-bit high-speed Static RAM organized as $512 \, \text{K} \times 8$. It is fabricated using IDT's high-perfomance, high-reliability CMOS technology. This state-of-the-art technology, combined with innovative circuit design techniques, provides a cost-effective solution for high-speed memory needs.

The IDT71V424 has an output enable pin which operates as fast as 5ns, with address access times as fast as 10ns. All bidirectional inputs and outputs of the IDT71V424 are TTL-compatible and operation is from a single 3.3V supply. Fully static asynchronous circuitry is used, requiring no clocks or refresh for operation.

The IDT71V424 is packaged in a 36-pin, 400 mil Plastic SOJ and 44-pin, 400 mil TSOP.

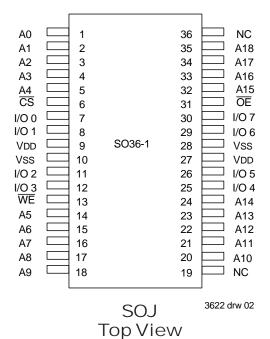
Functional Block Diagram



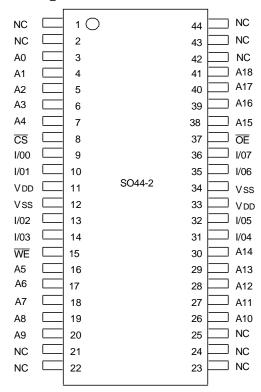
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Pin Configuration



Pin Configuration



TSOP Top View

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Pin Description

A0 - A18	Address Input Input			
CS	Chip Select Input			
WE	Write Enable	Input		
ŌĒ	Output Enable	Input		
I/O ₀ - I/O ₇	Data Input/Output	I/O		
VDD	3.3V Power	Power		
Vss	Ground	Gnd		

Capacitance

 $(TA = +25^{\circ}C, f = 1.0MHz, SOJ package)$

Symbol	Parameter ⁽¹⁾	Conditions	Max.	Unit
Cin	Input Capacitance	VIN = 3dV	7	pF
Cvo	I/O Capacitance	Vout = 3dV	8	pF

NOTE:

3622 tbl 02

1. This parameter is guaranteed by device characterization, but not production tested.

Truth Table(1,2)

CS	ŌĒ	WE	l/O	Function
L	L	Н	DATAout	Read Data
L	Х	L	DATAIN	Write Data
L	Н	Н	High-Z	Output Disabled
Н	Χ	Х	High-Z	Deselected - Standby (ISB)
V HC ⁽³⁾	Х	Х	High-Z	Deselected - Standby (ISB1)

3622 tbl 01

- NOTES: 1. $H = V_{IH}$, $L = V_{IL}$, x = Don't care.
- 2. $V_{LC} = 0.2V$, $V_{HC} = V_{DD} 0.2V$
- 3. Other inputs $\geq V_{HC}$ or $\leq V_{LC}$.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Rating Value			
VDD	Supply Voltage Relative to Vss	-0.5 to +4.6	V		
VIN, VOUT	Terminal Voltage Relative to Vss	-0.5 to VDD+0.5	V		
TBIAS	Temperature Under Bias	-55 to +125	°C		
Тѕтс	Storage Temperature	-55 to +125	۰C		
Рт	Power Dissipation	1	W		
Гоит	DC Output Current	50	mA		

NOTE:

3622 tbl 04

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Recommended Operating Temperature and Supply Voltage

Grade	Temperature	V ss	V DD
Commercial	0°C to +70°C	0V	See Below
Industrial	-40°C to +85°C	0V	See Below

3622 thi 0

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
VDD	Supply Voltage	3.0	3.3	3.6	V
Vss	Ground	0	0	0	٧
ViH	Input High Voltage	2.0	_	V _{DD} +0.3 ⁽¹⁾	V
VIL	Input Low Voltage	-0.3 ⁽²⁾		0.8	V

3622 tbl 06

NOTES:

- 1. Vih (max.) = Vdd+2V for pulse width less than 5ns, once per cycle.
- 2. VIL (min.) = -2V for pulse width less than 5ns, once per cycle.

DC Electrical Characteristics

(VDD = Min. to Max., Commercial and Industrial Temperature Ranges)

			IDT71V424		
Symbol	Parameter	Test Condition	Min. Max. Unit		
lu	Input Leakage Current	VDD = Max., VIN = Vss to VDD		5	μΑ
ILO	Output Leakage Current	VDD = Max., $\overline{\text{CS}}$ = VIH, VOUT = VSS to VDD		5	μΑ
Vol	Output Low Voltage	IOL = 8mA, VDD = Min.		0.4	V
Vон	Output High Voltage	Iон = -4mA, Vdd = Min.	2.4		V

3622 tbl 07

DC Electrical Characteristics(1, 2, 3)

(VDD = Min. to Max., VLC = 0.2V, VHC = VDD - 0.2V)

	Parameter				71V424	S/L 10	71V42	4S/L 12	71V424	S/L 15	l lmit
Symbol			Com'l.	Ind. ⁽⁵⁾	Com'l.	Ind. ⁽⁵⁾	Com'l.	Ind. ⁽⁵⁾	Unit		
laa	$\label{eq:Dynamic Operating Current} \frac{\text{Dynamic Operating Current}}{\overline{\text{CS}}} \leq \text{VLC, Outputs Open, Vdd} = \text{Max., } f = \text{fmax}^{(4)}$		180	180	170	170	160	160	mA		
lcc			165	_	155	155	145	145	mA		
lon	Dynamic Standby Power Supply Current $\overline{CS} \ge V$ HC, Outputs Open, VDD = Max., f = fMAX ⁽⁴⁾		60	60	55	55	50	50	mA		
ISR			55		50	50	45	45	mA		
lone	Full Standby Power Supply Current (static)		20	20	20	20	20	20	mA		
ISB1	$\overline{\text{CS}} \ge \text{V}_{\text{HC}}$, Outputs Open, $\text{V}_{\text{DD}} = \text{Max.}$, $f = 0^{(4)}$	L	10	_	10	10	10	10	mA		

NOTES:

3622 tbl 08

- 1. All values are maximum guaranteed values.
- 2. All inputs switch between 0.2V (Low) and VDD 0.2V (High).
- 3. Power specifications are preliminary.
- 4. fmax = 1/trc (all address inputs are cycling at fmax); f = 0 means no address input lines are changing.
- 5. Standard power 10ns (S10) speed grade only.

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	1.5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
AC Test Load	See Figure 1, 2 and 3

3622 tbl 09

AC Test Loads

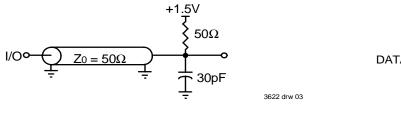
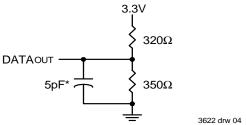


Figure 1. AC Test Load



*Including jig and scope capacitance.

Figure 2. AC Test Load (for tclz, tolz, tchz, tohz, tow, and twhz)

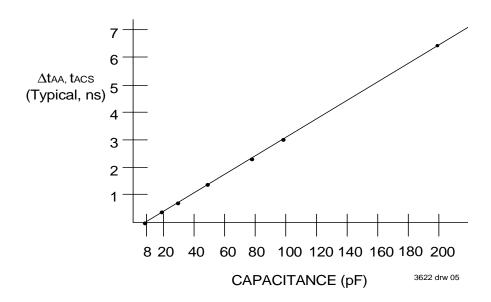


Figure 3. Output Capacitive Derating

AC Electrical Characteristics

(Vcc = 3.3V ± 10%, Commercial and Industrial Temperature Ranges)

		71V424	S/L10 ⁽²⁾	71V42	4S/L12	71V42	4S/L15	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYCLE								
trc	Read Cycle Time	10		12		15		ns
taa	Address Access Time		10		12		15	ns
tacs	Chip Select Access Time		10		12		15	ns
tclz ⁽¹⁾	Chip Select to Output in Low-Z	4		4		4		ns
tcHz ⁽¹⁾	Chip Deselect to Output in High-Z		5		6		7	ns
toe	Output Enable to Output Valid	_	5		6		7	ns
toLZ ⁽¹⁾	Output Enable to Output in Low-Z	0		0		0		ns
tonz ⁽¹⁾	Output Disable to Output in High-Z	_	5		6		7	ns
toн	Output Hold from Address Change	4		4		4		ns
tpu ⁽¹⁾	Chip Select to Power Up Time	0		0		0		ns
tPD ⁽¹⁾	Chip Deselect to Power Down Time	_	10		12		15	ns
WRITE CYCL	E							
twc	Write Cycle Time	10		12		15		ns
taw	Address Valid to End of Write	8		8		10		ns
tcw	Chip Select to End of Write	8		8		10		ns
tas	Address Set-up Time	0		0		0		ns
twp	Write Pulse Width	8		8		10		ns
twr	Write Recovery Time	0		0		0		ns
tow	Data Valid to End of Write	6		6		7		ns
tdH	Data Hold Time	0		0		0		ns
tow ⁽¹⁾	Output Active from End of Write	3		3		3		ns
twnz ⁽¹⁾	Write Enable to Output in High-Z		6		7		7	ns

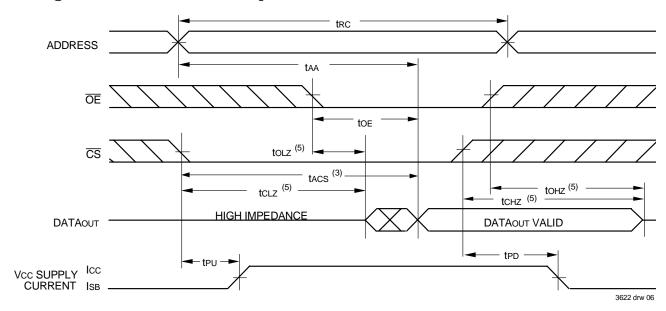
NOTES:

3622 tbl 10

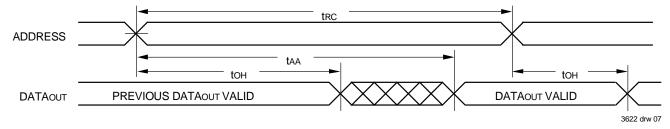
2. 0°C to +70°C temperature range only for low power 10ns (L10) speed grade.

^{1.} This parameter guaranteed with the AC load (Figure 2) by device characterization, but is not production tested.

Timing Waveform of Read Cycle No. 1(1)



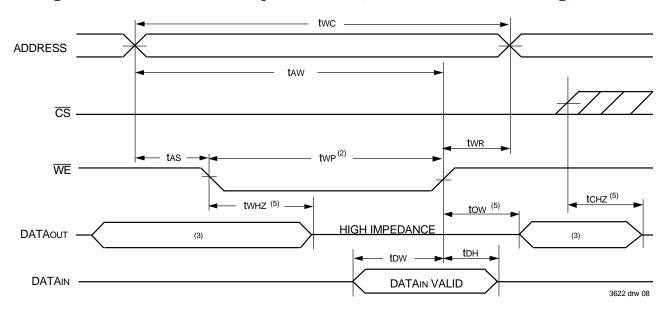
Timing Waveform of Read Cycle No. 2^(1, 2, 4)



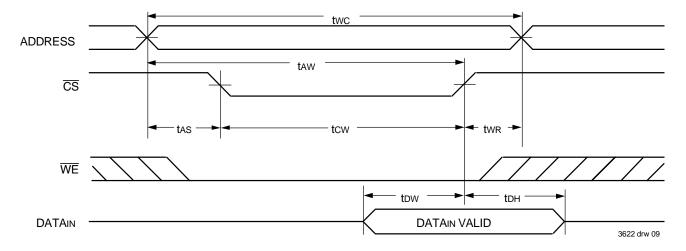
NOTES:

- 1. $\overline{\text{WE}}$ is HIGH for Read Cycle.
- 2. Device is continuously selected, $\overline{\text{CS}}$ is LOW.
- 3. Address must be valid prior to or coincident with the later of $\overline{\text{CS}}$ transition LOW; otherwise tax is the limiting parameter.
- 4. \overline{OE} is LOW.
- 5. Transition is measured ±200mV from steady state.

Timing Waveform of Write Cycle No. 1 (WE Controlled Timing)(1, 2, 4)



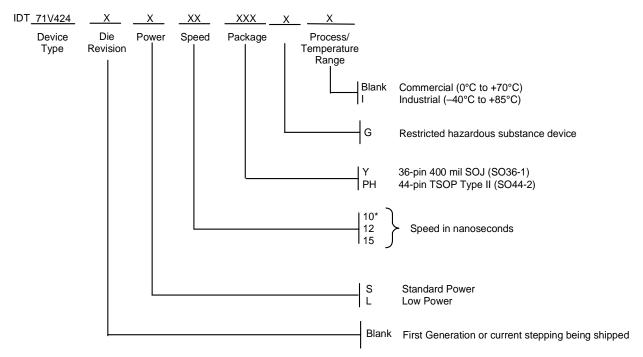
Timing Waveform of Write Cycle No. 2 (CS Controlled Timing)(1, 4)



NOTES:

- 1. A write occurs during the overlap of a LOW \overline{CS} and a LOW \overline{WE} .
- 2. $\overline{\text{OE}}$ is continuously HIGH. During a $\overline{\text{WE}}$ controlled write cycle with $\overline{\text{OE}}$ LOW, twp must be greater than or equal to twHz + tow to allow the I/O drivers to turn off and data to be placed on the bus for the required tow. If $\overline{\text{OE}}$ is HIGH during a $\overline{\text{WE}}$ controlled write cycle, this requirement does not apply and the minimum write pulse is the specified twp.
- 3. During this period, I/O pins are in the output state, and input signals must not be applied.
- 4. If the CS LOW transition occurs simultaneously with or after the WE LOW transition, the outputs remain in a high impedance state. CS must be active during the tow write period.
- 5. Transition is measured ±200mV from steady state.

Ordering Information



^{*} Commercial only for low power 10ns (L10) speed grade.

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Datasheet Document History

8/13/99		Updated to new format
	Pg. 2	Removed SO44-1 from TSOP pinout
	Pg. 7	Revised footnotes on Write Cycle No. 1 diagram
		Removed footnote for twn on Write Cycle No. 2 diagram
	Pg. 9	Added Datasheet Document History
8/31/99	Pg. 1–9	Added Industrial temperature range offerings
11/22/02	Pg. 8	Added die revision option to ordering information
07/31/03	Pg. 8	Updated note, L10 speed grade commercial temperature only and updated die stepping from YF to Y.
07/28/04	Pg. 3	Increased ISB for all "L" and S15 speeds by 10mA and increased for S12 speed by 5mA (refer to
		PCN# SR-0402-02).
	Pg. 8	Added "Restricted hazardous substance device" to the ordering information.



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